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SEMICONDUTORES LTDA.

## A1C:240S.XX.05

### VOLTAGE RATINGS

Part Number	$V_{RRM}$ , $VR - (V)$		$V_{RSM}$ , $V_R - (V)$	Max. non-rep. peak reverse voltage
	TJ = 0 to 150°C	TJ = -40 to 0°C		
A1C:240S.02.05	200	200	300	
A1C:240S.04.05	400	400	500	
A1C:240S.06.05	600	600	700	
A1C:240S.08.05	800	800	900	
A1C:240S.10.05	1000	1000	1100	
A1C:240S.12.05	1200	1200	1300	

This datasheet applies to:

Metric thread: A1C:240S.XX.05,  
A1D:240S.XX.05

Inch thread: A2C:240S.XX.05,  
A2D:240S.XX.05

### MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES
$T_J$ Junction Temperature	-40 to 150	°C	-
$T_{stg}$ Storage Temperature	-40 to 150	°C	-
$I_{F(AV)}$ Max. Av. current	240	A	180° half sine wave
@ Max. $T_C$	100	°C	
$I_{F(RMS)}$ Nom. RMS current	380	A	-
$I_{FSM}$ Max. Peak non-rep. surge current	5.75	kA	50 Hz half cycle sine wave
	6.27		Initial $T_J$ = 125°C, rated $V_{RRM}$ applied after surge.
	6.56		60 Hz half cycle sine wave
	7.15		50 Hz half cycle sine wave
			Initial $T_J$ = 125°C, no voltage applied after surge.
$I^2t$ Max. $I^2t$ capability	171.00	kA <sup>2</sup> s	$t = 10\text{ms}$
	187		$t = 8.3 \text{ ms}$
	195		$t = 10\text{ms}$
	213.00		$t = 8.3 \text{ ms}$
$I^{2t^{1/2}}$ Max. $I^{2t^{1/2}}$ capability	2340	$\text{A}^{2}\text{s}^{1/2}$	Initial $T_J$ = 125°C, no voltage applied after surge. $t_x = I^{2t^{1/2}} * t_x/2$ . (0.1 < $t_x$ < 10ms).
$I_{RRM}$ Maximum peak reverse current at rated $V_{RRM}$ .	1	mA	$T_J = 25^\circ\text{C}$
$I_{RM}$ Peak reverse recovery current	25	A	
$I_{FM}$ Peak forward current	240	A	
di/dt Max. Non-repetitive rate-of-rise current	50	$\text{A}/\mu\text{s}$	$T_J = 25^\circ\text{C}$ , $V_D = V_{DRM}$ , $I_{FM} = 240\text{A}$ .
F Mounting Force	30	N.m	-



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### CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
$V_{FM}$ peak on-state voltage	---	---	1.75	V	Initial $T_J = 25^\circ\text{C}$ , 50-60Hz half sine, $I_{peak} = 754\text{A}$ .
$V_{F(TO)}$ Threshold voltage	---	---	0.8	V	$T_J = 150^\circ\text{C}$
$r_F$ Slope resistance	---	---	1.15	$\text{m}\Omega$	
$t_{rr}$ Maximum reverse recovery time	---	---	1000	ns	$T_J = 25^\circ\text{C}$ , $I_F = 1\text{A}$ to $V_R = 30\text{V}$ , $-dI_F/dt = 25\text{A}/\mu\text{s}$
	---	---	2000		$T_J = 25^\circ\text{C}$ , $-dI_F/dt = 25\text{A}/\mu\text{s}$ , $I_{FM} = \pi \times \text{rated } I_{F(Av.)}$ .
$R_{thJC}$ Thermal resistance, junction-to-case	---	---	0.2	$^\circ\text{C}/\text{W}$	DC operation
$R_{thCS}$ Thermal resistance, case-to-sink	---	---	0.03	$^\circ\text{C}/\text{W}$	Mtg. Surface smooth, flat and greased. Single side cooled.
wt Weight	---	250(8.75)	---	g(oz.)	---
Case Style	---	DO-205AB (DO-9)	JEDEC		---

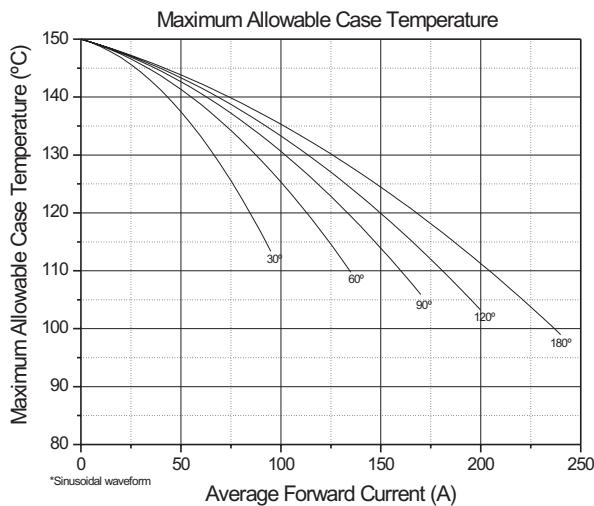


Fig. 1 - Current Ratings Characteristics

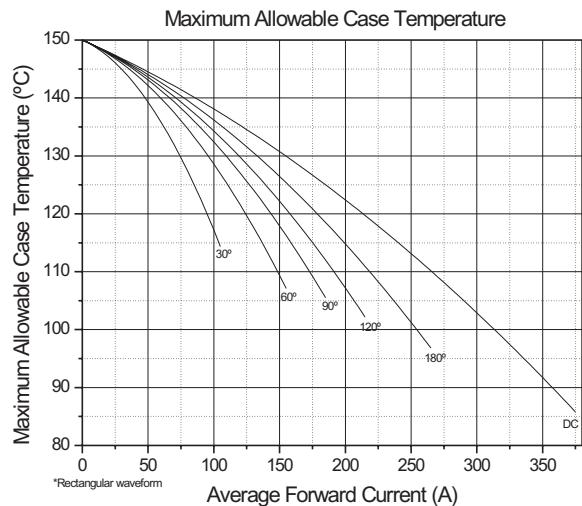


Fig. 2 - Current Ratings Characteristics

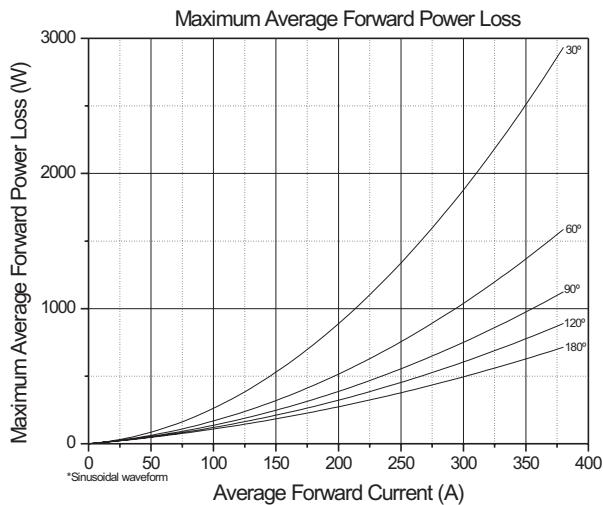


Fig. 3 - Forward Power Loss Characteristics

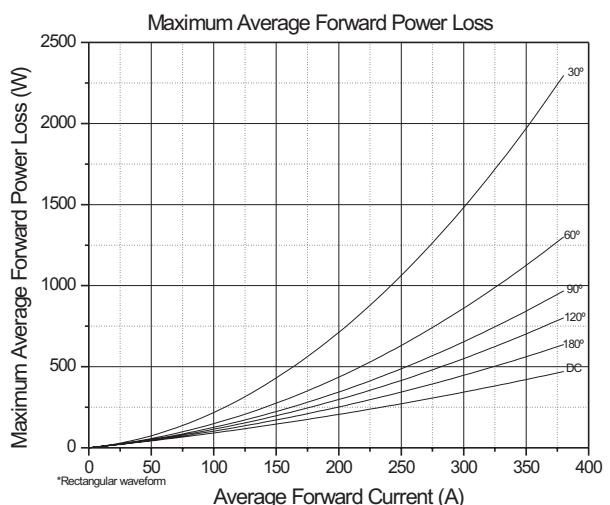
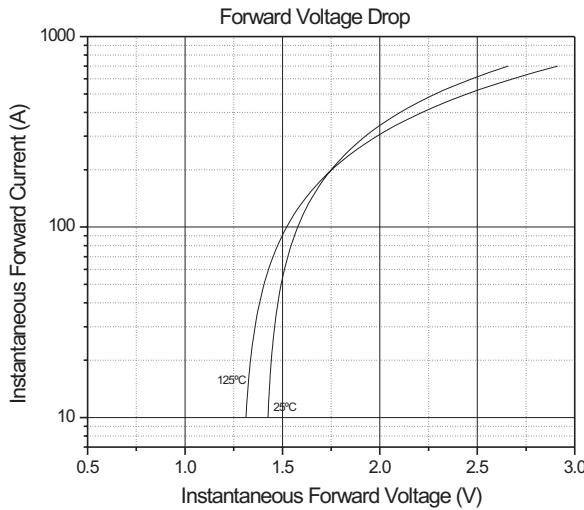


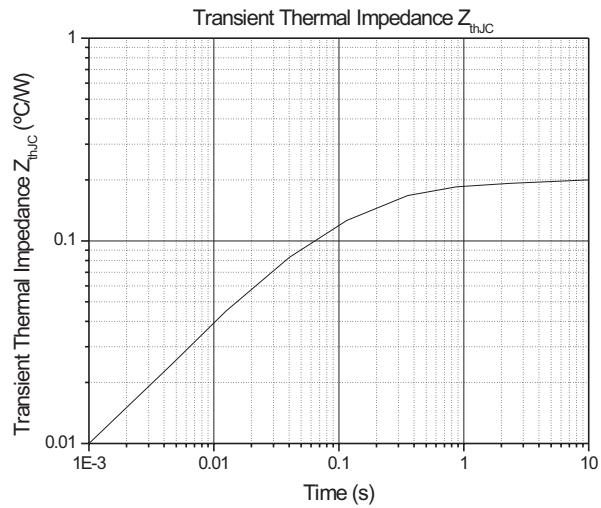
Fig. 4 - Forward Power Loss Characteristics



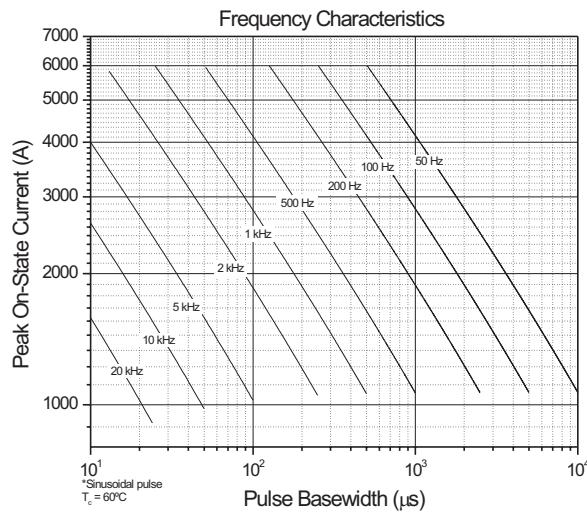
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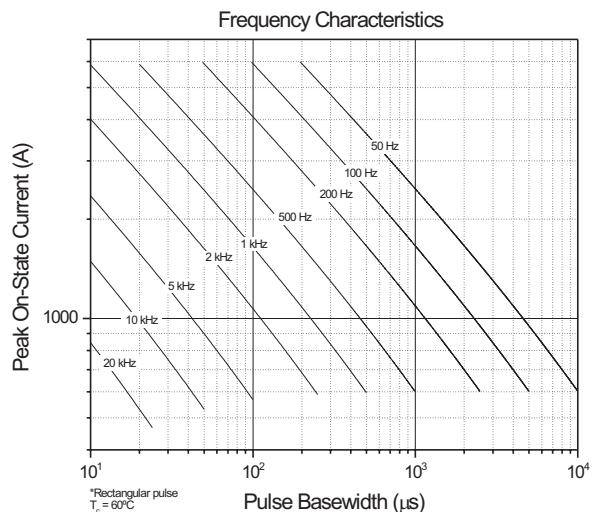
**Fig. 5 - Forward Voltage Drop Characteristics**



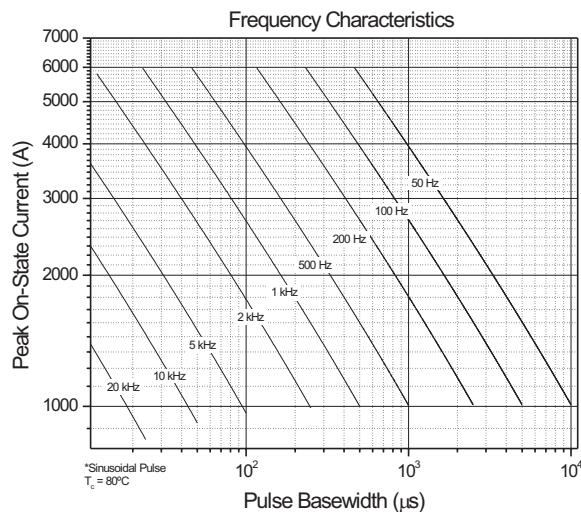
**Fig. 6 - Transient Thermal Impedance Characteristics**



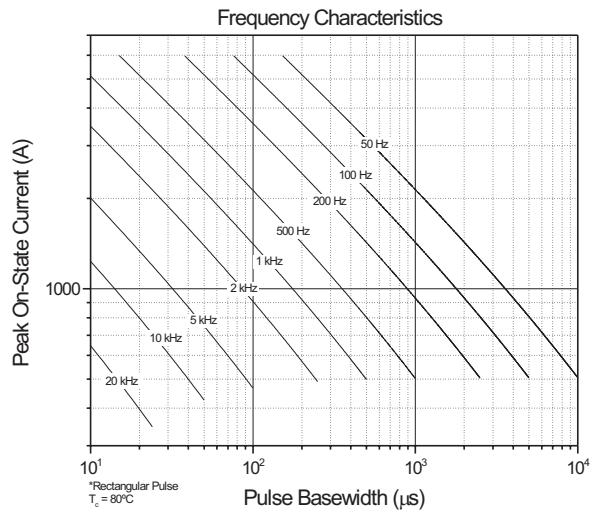
**Fig. 7 - Frequency Characteristics**



**Fig. 8 - Frequency Characteristics**



**Fig. 9 - Frequency Characteristics**

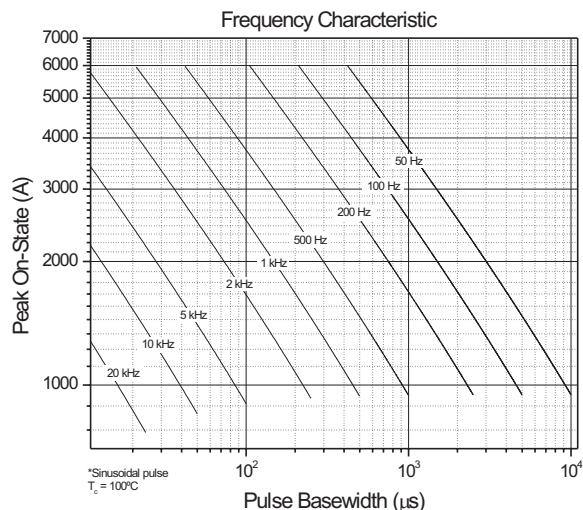


**Fig. 10 - Frequency Characteristics**

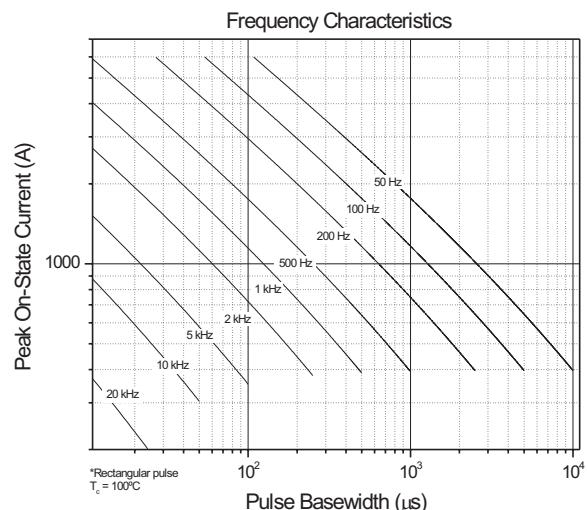


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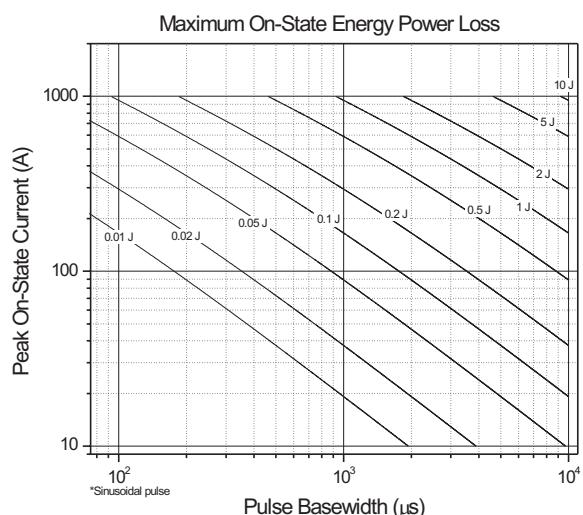
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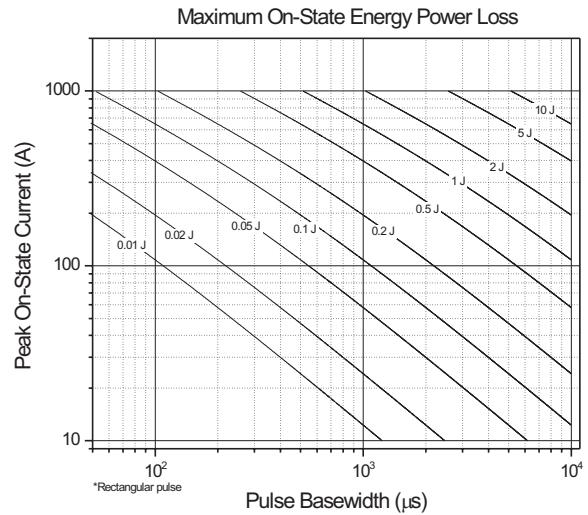
**Fig. 11 - Frequency Characteristics**



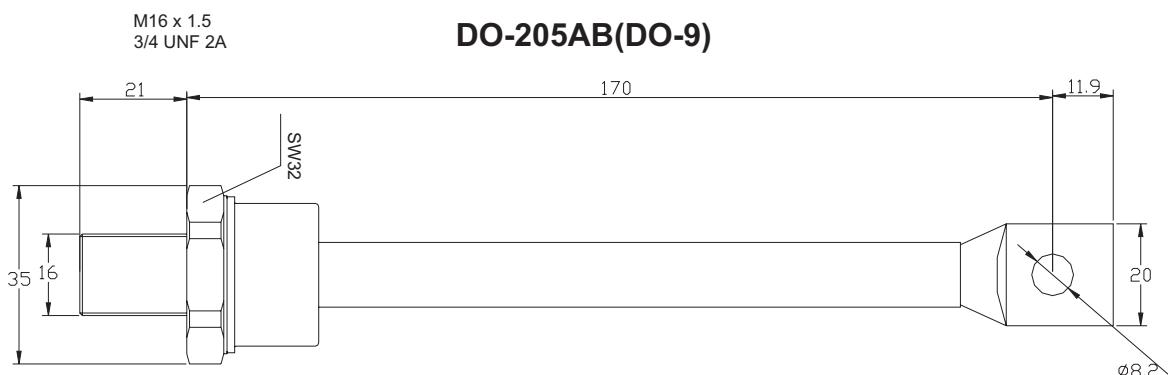
**Fig. 12 - Frequency Characteristics**



**Fig. 13 - Maximum On-State Power Loss Characteristics**



**Fig. 14 - Maximum On-State Power Loss Characteristics**



**Fig. 15 - Outline Characteristics**